


## CLAIMS

1. A transistor comprising elements of a bipolar static induction transistor disposed on both major surfaces of a silicon monocrystal substrate:  
an epitaxial layer, a gate, channels, sources, gate and source electrodes;  
impurity concentration near said gates is high enough: said gate, said channels, said sources are disposed in said epitaxial layer; donor concentration of said epitaxial layer equals of about  $10^{17} \text{ cm}^{-3}$ ;  
donor concentration of said substrate equals of about  $10^{14} \text{ cm}^{-3}$ ;  
one channel of the multielement structure is thicker than the other normally-off channels;  
said channel is connected to a separate electrode;  
said source electrodes are formed of n<sup>+</sup>-type polysilicon.

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05.01.2006

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